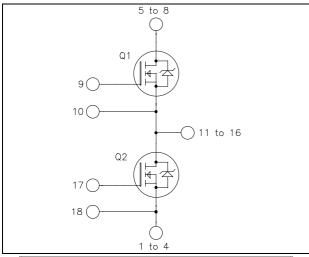


Phase leg Super Junction MOSFET Power Module

 $V_{DSS} = 600V$ $R_{DSon} = 24m\Omega \text{ max } @ \text{ Tj} = 25^{\circ}\text{C}$ $I_D = 95A$ @ Tc = 25°C



1 0 2 0 3 0 4 0 O 15 **9** 14 **o** 13 O 12 5 **o** 6 **o** 7 **o** 8 **o** 10 9 00

Pins 1/2/3/4; 5/6/7/8; 11/12/13/14/15/16 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- $CoolMOS^{TM}\\$
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Kelvin source for easy drive
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- **RoHS Compliant**

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		600	V
ī	Continuous Drain Current		95	
I_D	Continuous Drain Current	$T_c = 80$ °C	70	Α
I_{DM}	Pulsed Drain current	260		
V_{GS}	Gate - Source Voltage	±20	V	
R _{DSon}	Drain - Source ON Resistance	24	mΩ	
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	462	W
I_{AR}	Avalanche current (repetitive and non repetitive)		15	A
E _{AR}	Repetitive Avalanche Energy		3	mJ
E_{AS}	Single Pulse Avalanche Energy		1900	1113

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$			350	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 47.5A$			24	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 25V$			14.4		nF
C_{oss}	Output Capacitance	f = 1MHz			17		111
Q_{g}	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 300V$ $I_D = 95A$			300		пС
Q_{gs}	Gate – Source Charge				68		
Q_{gd}	Gate – Drain Charge				102		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 95A$ $R_G = 2.5\Omega$			21		ns
$T_{\rm r}$	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				100		
T_{f}	Fall Time				45		
E _{off}	Turn-off Switching Energy	Inductive switching $V_{GS} = 10V$; $V_{Bus} = 400V$	$T_j = 25$ °C		1040		μJ
		$I_D = 95A$; $R_G = 2.5\Omega$ $T_j = 125^{\circ}C$			1270		μυ
R_{thJC}	Junction to Case Thermal Resistance	· · · · · · · · · · · · · · · · · · ·				0.27	°C/W

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{S}	Continuous Source current		$Tc = 25^{\circ}C$		95		Α
1 _S	(Body diode)		$Tc = 80^{\circ}C$		70		А
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -95A$	1			1.2	V
dv/dt	Peak Diode Recovery 1					4	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -95A$	$T_j = 25^{\circ}C$		600		ns
Q_{rr}	Reverse Recovery Charge	$V_R = 350V$ $di_S/dt = 200A/\mu s$	$T_j = 25^{\circ}C$		34		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

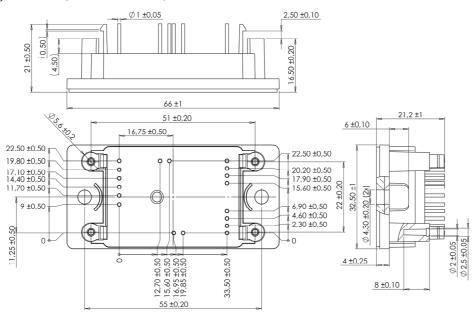
 $I_S \leq \text{- 95A} \qquad \text{di/dt} \leq 200 \text{A/}\mu \text{s} \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ}\text{C}$

Thermal and package characteristics

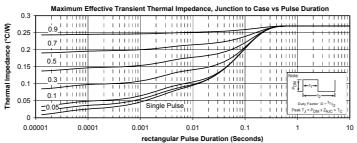
Symbol	Characteristic			Min	Typ	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

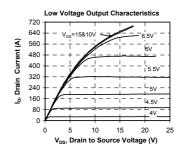


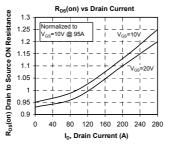
SP2 Package outline (dimensions in mm)

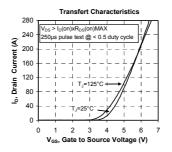


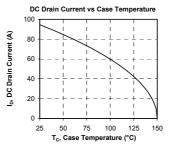
Typical Performance Curve



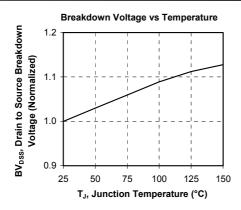


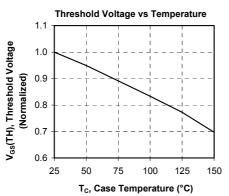


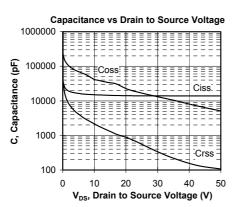


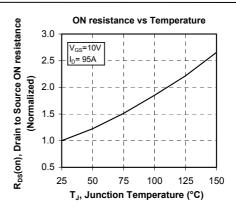


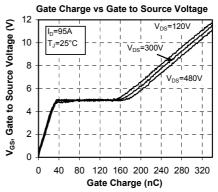




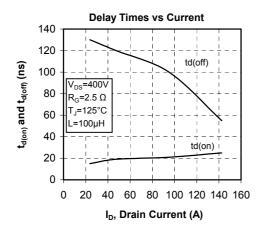


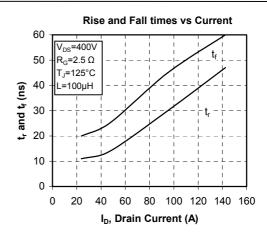


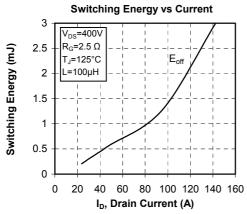


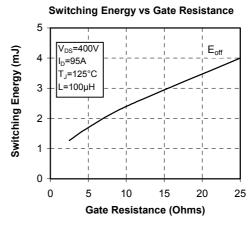


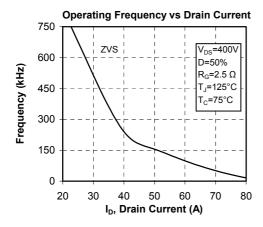


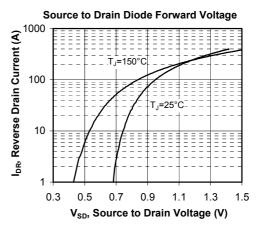












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